

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph [0003] on page 2, line 2, with the following amended paragraph:

[0003]

A silica polishing slurry using particularly silica particulates as the polish particles has been widely used as the polishing slurry for precision polish for a wiring formation or the like in the manufacture of a semiconductor integrated circuit (hereinafter, referred to semiconductor) because of little scratch generation of a surface to be polished. However, since the polishing speed of the silica polishing slurry is slow, attentions have been recently focused on a cerium oxide polishing slurry containing cerium oxide having a fast polishing speed (for example, see Japanese Patent Application Laid-Open Nos. 2000-26840 and ~~2-371267~~ 2002-371267). However, the cerium oxide polishing slurry has a problem of generating more scratches as compared with the silica polishing slurry.

Please replace the paragraph [00210] on page 6, line 18, with the following amended paragraph:

[0021]

Since the cerium oxide particles manufactured by the above method are easily flocculated, it is preferable that the cerium oxide particles are mechanically grinded. Preferable examples of grinding methods include a dry grinding method using a jet mill or the like, and a wet grinding method using a planet bead mill or the like. The jet mill is described in, for example, Chemical ~~Industrial~~ Engineering Paper Collection (Kagaku ~~Kogyo~~ Kougaku Ronbunshu), vol. 6, No. 5 (1980), 527-532.